

/ Descriptions

SOP-8 N MOS

N-Channel Enhancement Mode Field Effect Transistor in a SOP-8 Plastic Package.

/ Features

$V_{DS}(V)=30V$ $I_D=6.9A$

$R_{DS(ON)} < 32m\Omega (V_{GS}=10V)$

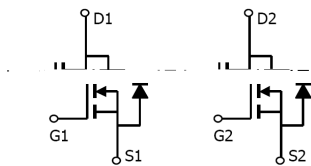
$R_{DS(ON)} < 36m\Omega (V_{GS}=4.5V)$

$R_{DS(ON)} < 52m\Omega (V_{GS}=2.5V)$

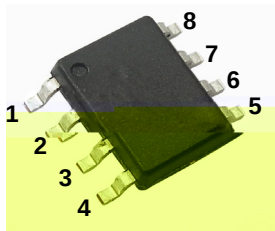
/ Applications

Power Management in Notebook computer, Portable Equipment and Battery powered systems and this device is suitable for use as a load switch or in PWM applications.

/ Equivalent Circuit



/ Pinning



PIN1	S2	PIN 2	G2	PIN 3	S1	PIN 4	G1
PIN 5	D1	PIN 6	D1	PIN 7	D2	PIN 8	D2

/ Marking

See Marking Instructions.

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current ^A	$I_D (T_a=25^{\circ}\text{C})$	6.9	A
	$I_D (T_a=70^{\circ}\text{C})$	5.8	A
Pulsed Drain Current ^B	I_{DM}	40	A
Power Dissipation for Single Operation ^A	$P_D (T_a=25)$	2.0	W
	$P_D (T_a=70)$	1.44	W
Junction and Storage Temperature Range	T_j, T_{stg}	-55 +150	$^{\circ}\text{C}$
Thermal Resistance-Junction to Ambient ^A	$R_{\theta JA} \quad t \leq 10s$	62.5	$^{\circ}\text{C/W}$
	$R_{\theta JA}$	110	$^{\circ}\text{C/W}$
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	40	$^{\circ}\text{C/W}$

Note:

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The value in any a given application depends on the user's specific board design. The current rating is based on the $t \leq 10s$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

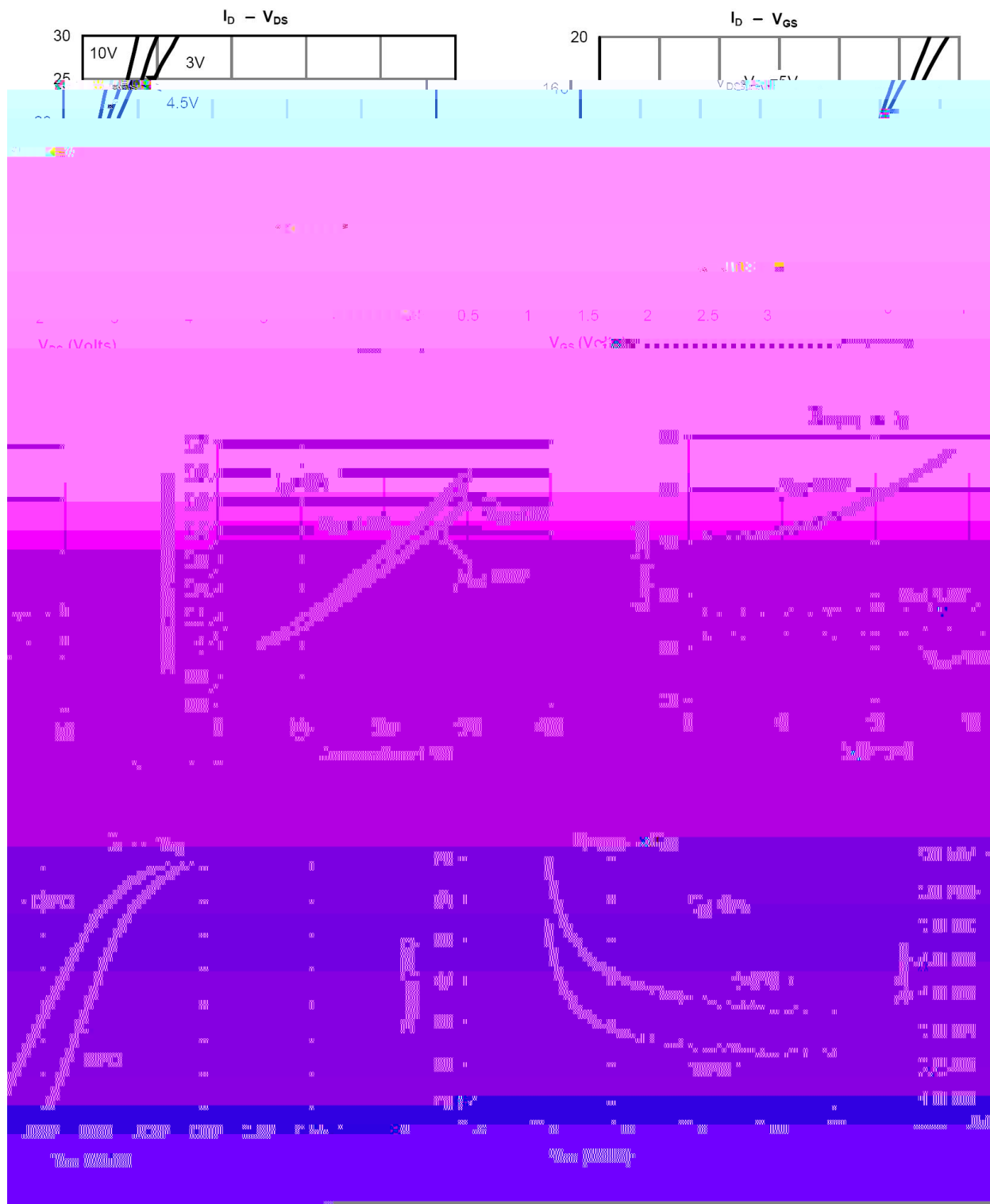
D. The static characteristics in Figures 1 to 6 are obtained using 80 μs pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The SOA curve provides a single pulse rating.

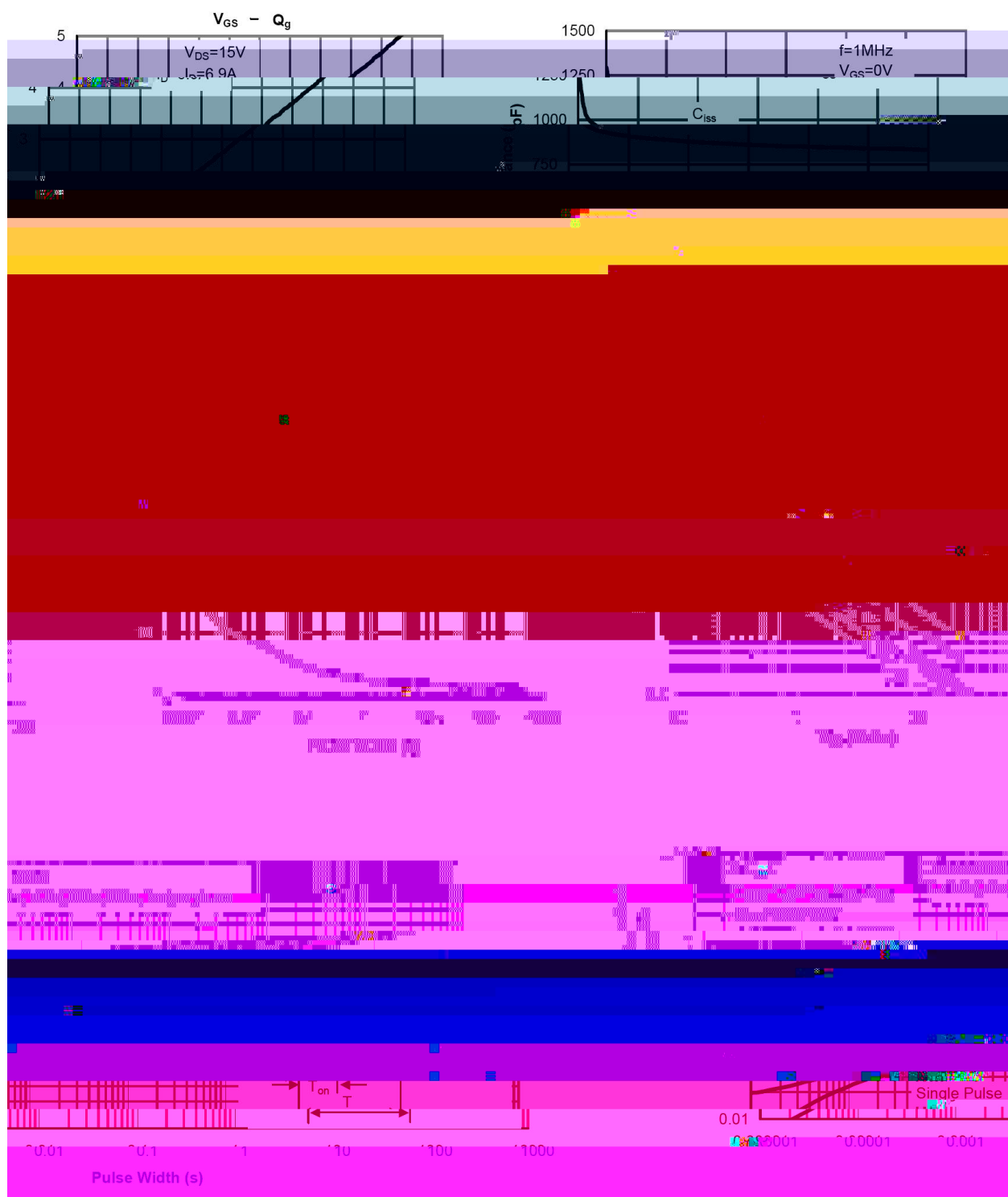
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu A$ $V_{GS}=0V$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=24V$ $V_{GS}=0V$			1.0	μA
		$V_{DS}=24V$ $V_{GS}=0V$ $T_J=55^\circ C$			5.0	
Gate-Body leakage current	I_{GSS}	$V_{DS}=0V$ $V_{GS}=\pm 12V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	0.7	1.1	1.4	V
On state drain current	$I_{D(ON)}$	$V_{GS}=4.5V$ $V_{DS}=5.0V$	6.9			A
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V$ $I_D=6.9A$		24	32	m Ω
		$V_{GS}=10V$ $I_D=6.9A$ $T_J=125^\circ C$		32.3	38	
		$V_{GS}=4.5V$ $I_D=6.0A$		27	36	
		$V_{GS}=2.5V$ $I_D=5.0A$		40	52	
Forward Transconductance	g_{FS}	$V_{DS}=5.0V$ $I_D=5.0A$	10	15		S
Diode Forward Voltage	V_{SD}	$I_S=1.0A$		0.77	1.0	V
Maximum Body-Diode Continuous Current	I_S				3.0	A
Total Gate Charge	Q_g	$V_{GS}=4.5V$ $V_{DS}=15V$ $I_D=6.9A$		9.6		nC
Gate-Source Charge	Q_{gs}			1.65		
Gate-Drain Charge	Q_{gd}			3.0		
Gate Resistance	R_g	$V_{GS}=0V$ $V_{DS}=0V$ $f=1MHz$		1.24		Ω
Input Capacitance	C_{iss}	$V_{GS}=0V$ $V_{DS}=15V$ $f=1MHz$		858		pF
Output Capacitance	C_{oss}			110		
Reverse Transfer Capacitance	C_{rss}			80		
Turn-on Delay Time	$t_{d(ON)}$	$V_{GS}=10V$ $V_{DS}=15V$ $R_L=2.2\Omega$ $R_{GEN}=6.0\Omega$		5.7		ns
Turn-on Rise Time	t_r			13		
Turn-off Delay Time	$t_{d(OFF)}$			37		
Turn-off Fall Time	t_f			4.2		
Body Diode Reverse Recovery Time	t_{rr}	$I_F=5.0A$ $dI/dt=100A/\mu s$		15.5		ns
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F=5.0A$ $dI/dt=100A/\mu s$		7.9		nC

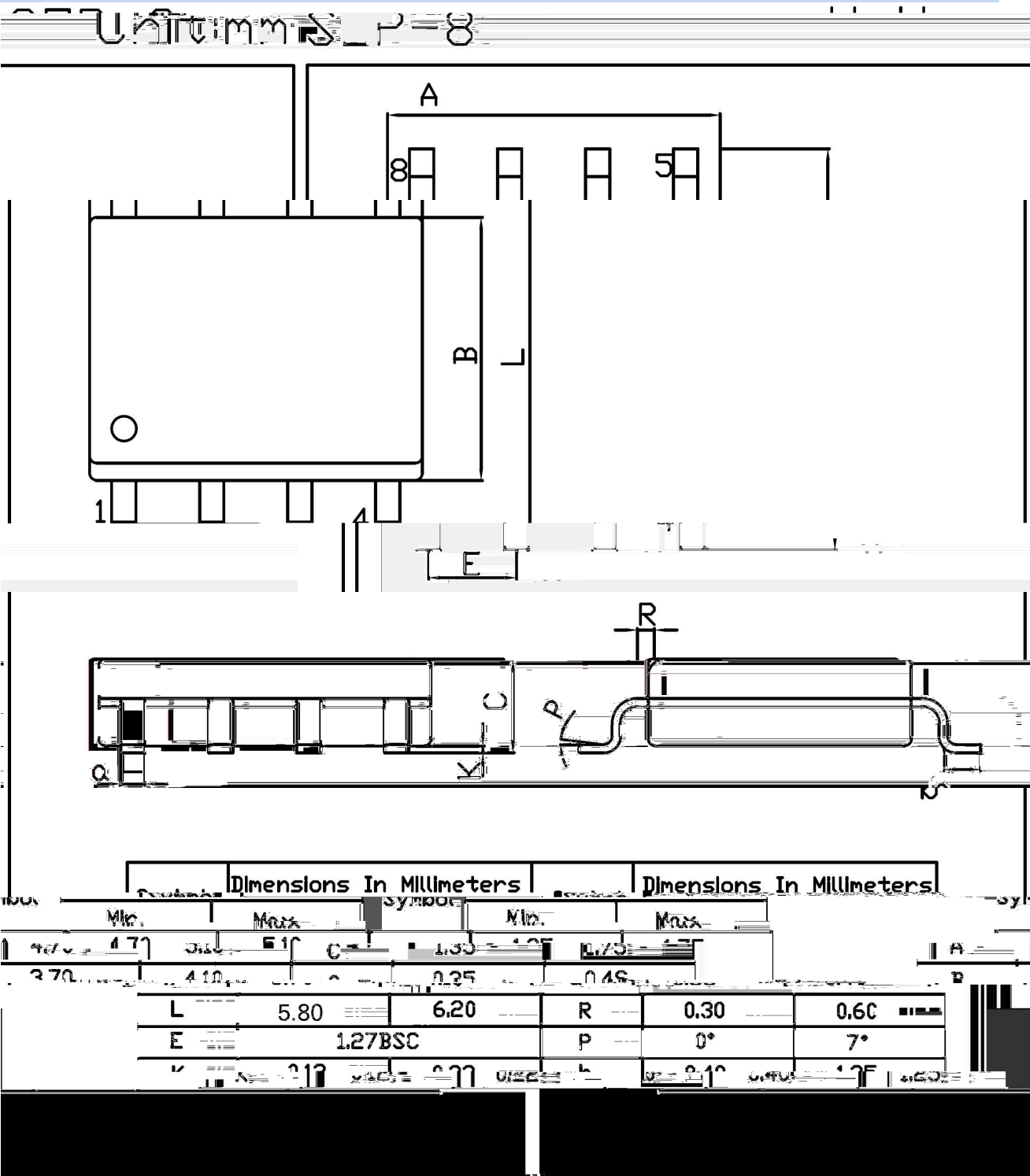
/ Electrical Characteristic Curve



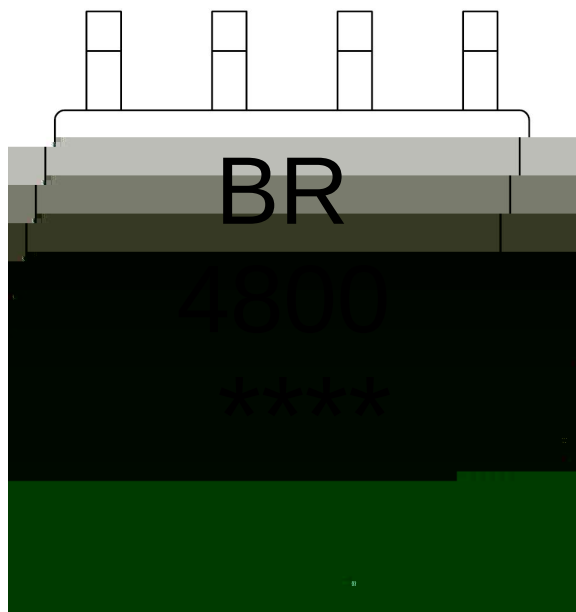
Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



BR

4800

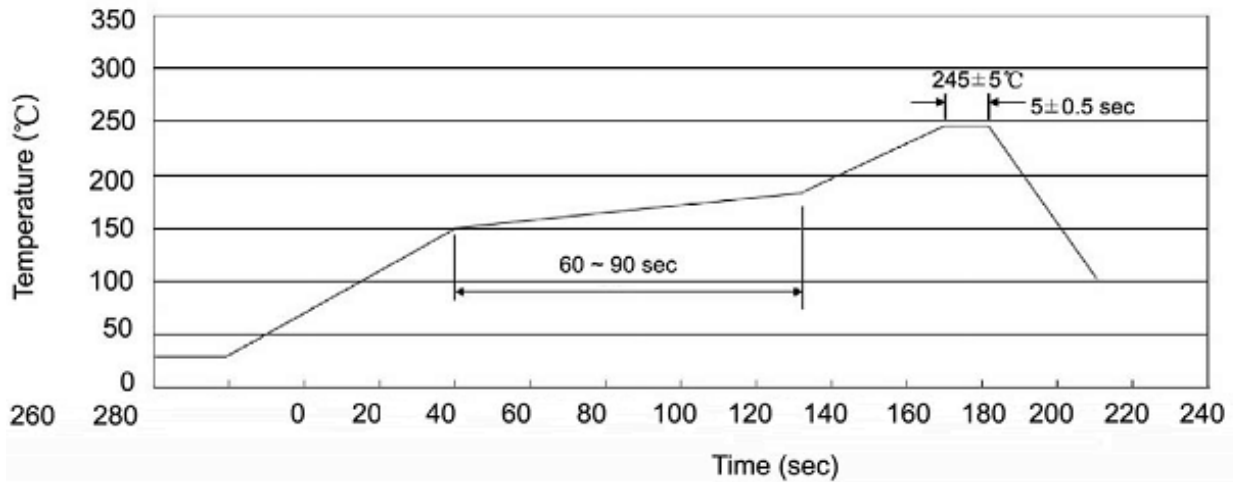
Note:

BR: Company Code.

4800: Product Type

****: Lot No. Code, code change with Lot No.

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Note:

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|---|-------|-----|-----------|----------|---|
| 1 | 150 | 180 | 60 | 90sec; | 1.Preheating:150~180 , Time:60~90sec. |
| 2 | 245±5 | | 5±0.5sec; | | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 | | | 2 | 10 /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

260±5 10±1 sec. Temp.:260±5℃ Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units					Dimension		(unit mm ³)

/ Notices